

# THE GEORGE WASHINGTON UNIVERSITY

WASHINGTON, DC

SCHOOL OF ENGINEERING AND APPLIED SCIENCE  
DEPARTMENT OF ELECTRICAL AND COMPUTER ENGINEERING  
ECE 2115: ENGINEERING ELECTRONICS LABORATORY

## Tutorial #5: Designing a Common-Emitter Amplifier

### BACKGROUND

There are two popular types of Common-emitter amplifiers:

1. Common-Emitter Amplifier without Emitter Degeneration
  - Sometimes called **grounded emitter** or simply **common-emitter**
  - This is the type you built in Lab 6
2. Common-Emitter Amplifier with Emitter Degeneration
  - Sometimes called **common-emitter with emitter resistor**
  - There are three possible configurations of this circuit:
    - i. Non-bypassed emitter resistor
    - ii. Bypassed emitter resistor with series external emitter resistor
    - iii. Bypassed emitter resistor with parallel external emitter resistor

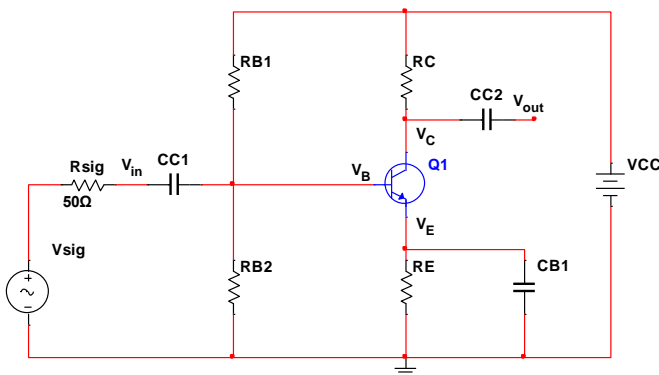


Figure 1 – CE without Emitter Degeneration

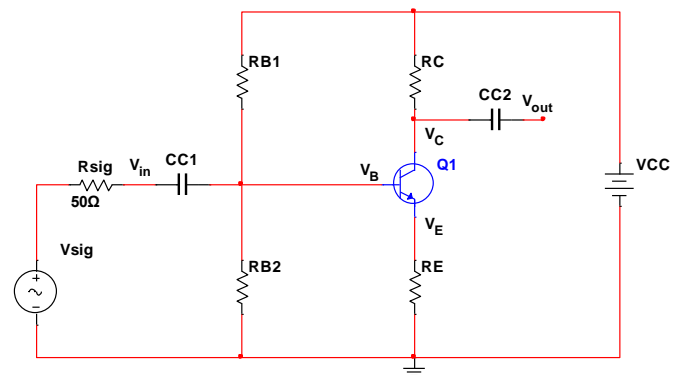


Figure 2 – CE with Emitter Degeneration (no bypass cap)

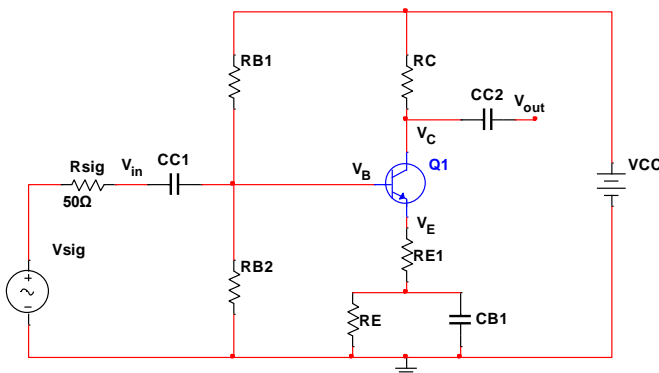


Figure 3 – CE with Emitter Degeneration Series Resistor

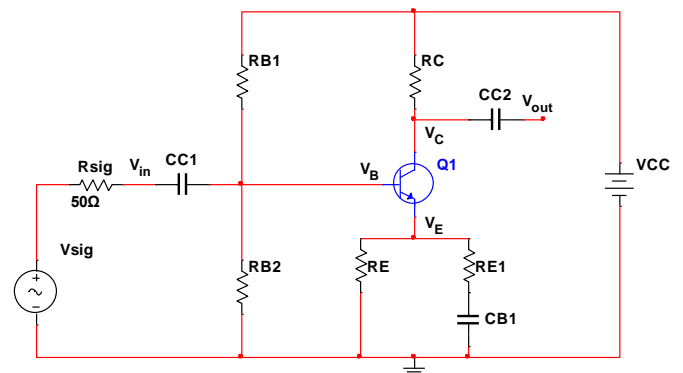


Figure 4 – CE with Emitter Degeneration Parallel Resistor

The two forms of the common-emitter amplifier and their various configurations have their own advantages and disadvantages when compared to one another. From the perspective of this tutorial, we will concentrate on the way “gain” is controlled for each of the circuits. No matter the configuration, for any common-emitter amplifier, the **input signal** is always through the **base terminal**, the **output** is always taken from the **collector terminal**, and the **emitter** is always “**common**” to both the input and output.

For Type 1 (CE without emitter degeneration) from **Figure 1**, the bypass capacitor  $C_{B1}$  shorts the **emitter** to **ground** for high frequency signals, hence the name “**grounded emitter**.” This amplifier is discussed in Sedra p.427-431. The voltage gain of this amplifier (when no load is present) is  $A_v = -g_m R_C$ . The designer can only control the value of  $R_C$ , and to some extent  $g_m$ , to control the voltage gain of the amplifier. This is the type you built in Lab 6 during the common-emitter portion of the lab.

For Type 2a (CE with emitter degeneration – non-bypassed emitter resistor) shown in **Figure 2**, there is no bypass capacitor. The emitter terminal is “common” to both the input and output through the resistor connected to the emitter ( $R_E$ ). The emitter resistor ( $R_E$ ) serves to give bias stability to the circuit. This amplifier is discussed in Sedra p.432-435. The gain of this amplifier when no load is present is  $A_v = -\alpha \frac{R_C}{r_e + R_E}$  or more simply  $A_v \approx -\frac{R_C}{r_e + R_E}$ . The designer can now use  $R_C$  and  $R_E$  to control the voltage gain of the amplifier.

For Type 2b (CE with emitter degeneration – bypassed emitter resistor with series emitter resistor) shown in **Figure 3**, the bypass capacitor shorts the resistor  $R_{E1}$  to ground for high frequency signals. The emitter terminal is “common” to both the input and output through the resistor ( $R_{E1}$ ). The emitter resistor ( $R_{E1}$ ) serves to give bias stability to the circuit. This amplifier is not discussed in Sedra. The gain of this amplifier when no load is present is  $A_v \approx -\frac{R_C}{r_e + R_{E1}}$ . The designer typically leaves  $R_C$  and uses  $R_{E1}$  to control the voltage gain of the amplifier.

For Type 2c (CE with emitter degeneration – bypassed emitter resistor with parallel emitter resistor) shown in **Figure 4**, the bypass capacitor shorts the resistor  $R_{E1}$  to ground for high frequency signals. Typically,  $R_{E1}$  is much smaller than  $R_E$ , making it so  $R_E$  is bypassed by comparison to  $R_{E1}$ .  $R_{E1}$  is an easier “path to ground” than for AC signals. The emitter terminal is “common” to both the input and output through the resistor ( $R_{E1}$ ). This amplifier is not discussed in Sedra. The gain of this amplifier when no load is present is  $A_v \approx -\frac{R_C}{r_e + R_{E1}}$ . The designer typically leaves  $R_C$  and uses  $R_{E1}$  to control the voltage gain of the amplifier. The advantage of this design is that  $R_{E1}$  serves no purpose in the DC biasing of the amplifier, so the designer only sets the value of  $R_{E1}$  after the DC bias has been determined for the amplifier.

Students are encouraged to use any of the common-emitter amplifier configurations shown above in labs and projects. Type 2 will be covered in this tutorial because it is stable, easiest to bias, and the gain can be adjusted without affecting its DC bias.

## INSTRUCTIONS

### Designing a Common-Emitter Amplifier with Emitter Degeneration Parallel Emitter Resistor

**Problem:** Design a common-emitter amplifier using the 2N3904 transistor that meets the following specs:

- $I_C = 2\text{mA}$
- $V_{CC} = 30\text{V}$
- $A_V$  (unloaded) =  $-50\text{ V/V}$
- $R_{in} = 4\text{k}\Omega$
- $R_L = 1\text{k}\Omega$
- $V_{in} = 10\text{mV @ } 10\text{kHz}$

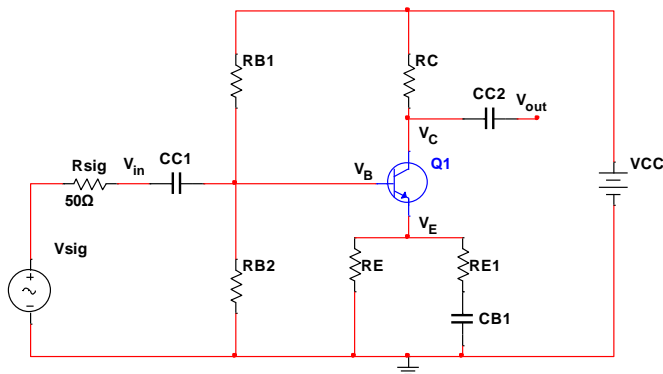


Figure 1.1 – Complete Common-Emitter Amplifier

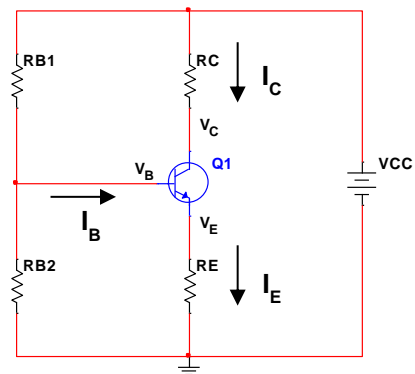


Figure 1.2 – Common-Emitter Amplifier (DC Only)

1. **Begin** with the skeleton of the amplifier we would like to design shown in **Figure 1.1**.
  - a. Our goal as designers will be to determine values for  $R_C$ ,  $R_E$ ,  $R_{E1}$ ,  $R_{B1}$ ,  $R_{B2}$ ,  $C_{C1}$ ,  $C_{C2}$ , and  $C_{B1}$  based on the specs given. We begin by determining the values of  $R_C$ ,  $R_E$ ,  $R_{B1}$ , and  $R_{B2}$  to provide DC bias to the transistor. Then, we view the circuit from an AC perspective to determine the size of  $R_{E1}$  to set the 'gain' for the amplifier.
  - b. From a DC perspective, the amplifier looks like the circuit in **Figure 1.2**. This is because the impedance of  $C_{C1}$ ,  $C_{C2}$ , and  $C_{B1}$  at DC ( $\approx 0\text{Hz}$ ) is nearly infinite. So, the capacitors look like open circuits at DC. This is why  $R_{E1}$  disappears from the circuit.
  - c. **Figure 1.2** looks just like what we did in Lab 6, except we are now solving the problem in reverse.

2. **Determine** the value of  $R_C$ .

- a. Because we take the output voltage from  $V_C$ , we start with the equation for  $V_C$ :

$$V_C = V_{CC} - I_C R_C$$

- b. The maximum output voltage we can have when  $I_C = 0\text{mA}$  is  $30\text{V}$  ( $V_{CC}$ ). The minimum output voltage we can have when  $I_C$  is at its highest, which makes  $V_C = 0\text{V}$ . We want the AC signal that comes out to “swing” symmetrically around the mid-point ( $\frac{1}{2} V_{CC}$ ).

$$\text{We set } V_C = \frac{1}{2} V_{CC} = \frac{1}{2} 30\text{V} = 15\text{V}$$

- c. Since  $I_C$  is given as  $2\text{mA}$ , we can use Ohm’s Law to determine  $R_C$ :

$$R_C = \frac{V_{CC} - V_C}{I_C} = \frac{30\text{V} - 15\text{V}}{2\text{mA}} = 7.5\text{k}\Omega$$

3. **Determine** the “Q” point of the transistor.

- a. From the test bench we created in Lab 5 to characterize the 2N3904 transistor, we perform a parametric sweep simulation to obtain the IV curve for the transistor. We sweep  $V_{CE}$  from 0 to  $V_{CC}$  ( $30\text{V}$ ). I have swept current  $I_B$  from 0 to  $20\mu\text{A}$ , in steps of  $2.3\mu\text{A}$ . I used trial and error until I was able to get a curve to tell me what  $I_B$  was when  $I_C = 2\text{mA}$  and  $V_{CE} = 15\text{V}$ .

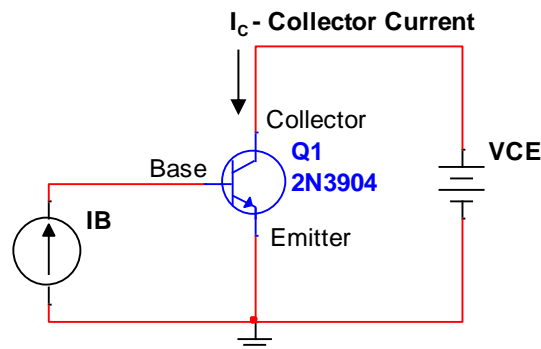


Figure 1.3 – BJT Test Circuit

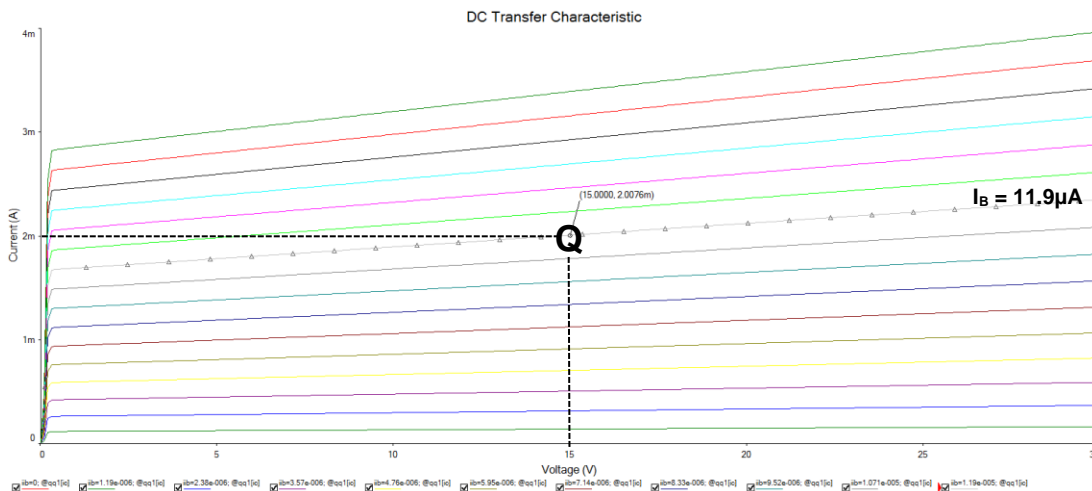


Figure 1.4 – IV Curve ( $I_C$  vs.  $V_{CE}$ ) for the 2N3904 BJT

In the specs, we were told  $I_C = 2\text{mA}$ . We determined that  $V_C = 15\text{V}$  in the last step. That is our “**quiescent value**” or **Q value**. From the IV curve, we can see that the 2N3904 transistor will supply  $\sim 2\text{mA}$  of current when the base current is set to  $I_B = 11.9\mu\text{A}$ . With this information, we can determine  $I_E$ ,  $R_{B1}$ ,  $R_{B2}$ , and  $R_E$ . So far we know:

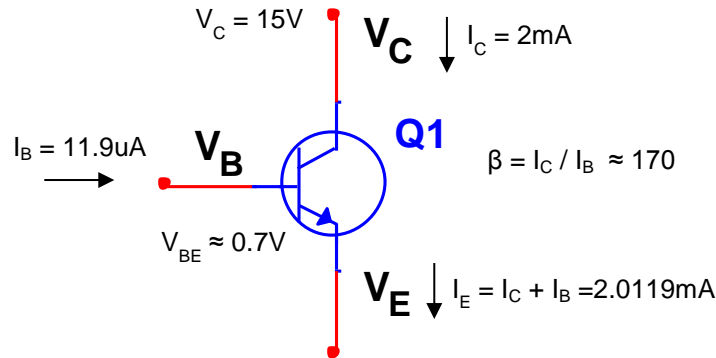


Figure 1.5 – DC Bias State for the 2N3904

4. Find  $R_E$ ,  $V_E$ , and  $V_B$ .

- a. As a rule of thumb for this type of common-emitter amplifier, we make  $R_E$  10% of  $R_C$ .

$$R_E = 10\%R_C = 0.1 * 7.5k\Omega = 750\Omega$$

- b. From Ohm’s Law, we can find  $V_E$  and  $V_B$ :

$$V_E = I_E R_E = 2.0119\text{mA} * 750\Omega \approx 1.5\text{V}$$

$$V_B = V_E + V_{BE} = 1.5\text{V} + 0.7\text{V} \approx 2.2\text{V}$$

5. Use  $V_{CC}$ ,  $V_B$ ,  $I_B$ , and  $R_{in}$  to find  $R_{B1}$  and  $R_{B2}$ .

- a. Our goal is to deliver  $11.9\mu\text{A}$  to the base of the transistor.  $R_{B1}$  and  $R_{B2}$  must be properly sized to achieve this goal.
- b. We generate three equations to find  $R_{B1}$  and  $R_{B2}$ .
- c. Since  $R_{B1}$  and  $R_{B2}$  are in parallel (as we learned from Lab 6’s tutorial), we know:

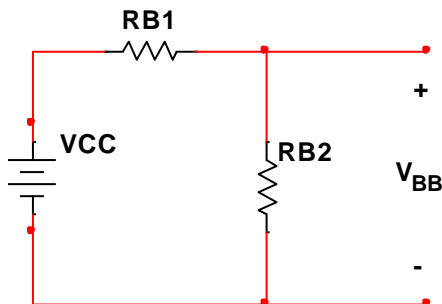


Figure 1.6 – Finding Thévenin Equivalent

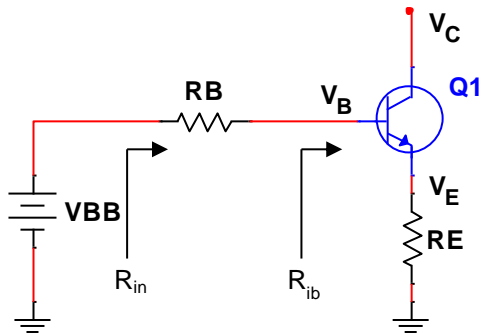
The Thévenin Voltage ( $V_{BB}$ ) is:

$$V_{BB} = \left( \frac{R_{B2}}{R_{B1} + R_{B2}} \right) V_{CC} \tag{1}$$

The Thévenin Resistance ( $R_B$ ) is:

$$R_B = R_{B1} || R_{B2} = \frac{R_{B1} R_{B2}}{R_{B1} + R_{B2}} \tag{2}$$

- d. Using the Thévenin equivalent resistance ( $R_B$ ) for  $R_{B1}$  and  $R_{B2}$  (as we did in Lab 6), we know our circuit can be redrawn to look like this:



Using Ohm's Law:

$$I_B = \frac{V_{BB} - V_B}{R_B}$$

$$V_{BB} = I_B R_B + V_B \quad (3)$$

Figure 1.7 – Redrawn with Thévenin Equivalent

- e. In **Equations 1-3**, we know  $V_{CC}$ ,  $I_B$ , and  $V_B$ , but we do not know  $R_{B1}$ ,  $R_{B2}$ ,  $R_B$ , or  $V_{BB}$ . Therefore, we have **four** unknowns, but only **three** equations. We need to find the value of one of these variables to solve for them all. We can use the given spec value for  $R_{in}(DC)$  to find the value of  $R_B$ .
- f. From the Thévenin equivalent figure above, we can see that:

$$R_{in} = R_B || R_{ib} \quad (4)$$

- g.  $R_{ib}$  is the input resistance looking into the **base** of the transistor. Since only  $R_E$  is attached to the emitter at DC (because  $R_{E1} + C_{B1}$  appears as an infinite load at DC), we can use the value found in Sedra on p. 457 for  $R_{ib}$ :

$$R_{ib} = (\beta + 1)(r_e + R_E)$$

We know from Sedra (p. 407), that:

$$r_e = \frac{V_T}{I_E} = \frac{26mV}{2.0119mA} \approx 13\Omega$$

This makes  $R_{ib}$ :

$$\begin{aligned} R_{ib} &= (\beta + 1)(r_e + R_E) \\ &= (171)(13\Omega + 750\Omega) \\ &\approx 130k\Omega \end{aligned}$$

- h. Using  $R_{ib}$  and  $R_{in}$ , from **Equation 4**, we can solve for  $R_B$ :

$$R_B = \frac{R_{in} R_{ib}}{R_{ib} - R_{in}} \approx 3.9k\Omega$$

- i. With  $R_B$  found, we can use **Equations 1-3** and some algebra to find  $R_{B1}$  and  $R_{B2}$ :

$$\begin{aligned} R_{B1} &= 51.8k\Omega \\ R_{B2} &= 4.2k\Omega \end{aligned}$$

- j. All the biasing resistors, currents, and voltages have now been found!

6. **Use  $R_{E1}$**  to set the **gain** for the common-emitter amplifier.
- a. The gain for this type of common-emitter amplifier is (with no load attached):

$$A_V(\text{unloaded}) = -\left(\frac{R_C}{r_e + R_E || R_{E1}}\right)$$

- b. The specs require  $A_V(\text{unloaded})$  to be equal to -50, so with some algebra, we can solve for  $R_{E1}$ :

$$R_{E1} = 168\Omega$$

7. **Determine** the **gain** when the load is attached.
- a. The gain for this type of common-emitter amplifier is (with load attached):

$$A_V(\text{loaded}) = -\left(\frac{R_C || R_L}{r_e + R_E || R_{E1}}\right) \approx -6$$

8. **Set** values for  $C_{C1}$ ,  $C_{C2}$ , and  $C_{B1}$ .
- a. The impedance of a capacitor is  $Z_C = \frac{1}{j2\pi fC}$ . We can use this knowing that we want  $C_{C1}$ ,  $C_{C2}$ , and  $C_{B1}$  to all look like “shorts” at 10kHz (the input frequency), and select a value that we have in the ECE 2115 kit.